

AMENDMENTS TO THE CLAIMS:

Please cancel claims 2 and 8, without prejudice or disclaimer of their subject matter, and amend claims 1, 3, 7, and 9 as indicated below. This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A semiconductor apparatus comprising:
 - a substrate;
 - a buffer layer made of a monocrystal semiconductor material and formed on the substrate;
 - a strained-Si layer formed on the buffer layer and having a lattice constant different from that of the buffer layer;
 - a monocrystal insulating film formed on the strained-Si layer, the monocrystal insulating film being made of a material having a rare earth structure with a lattice constant different from that of Si; and
 - [[an]] a monocrystal semiconductor electrode formed on the insulating film.
2. (Cancelled)
3. (Currently Amended) The semiconductor apparatus according to claim [[2]] 1, wherein the monocrystal semiconductor electrode is made of ~~erystalline~~ monocrystal SiGe.

4. (Previously Presented) The semiconductor apparatus according to claim 1, wherein the insulating film is a monocrystal film including one selected from the group consisting of CeO₂, PrO₂, CaO₂, TbO₂, PrO₂, Dy₂O₃, Er₂O₃, Eu₂O₃, Gd₂O₃, Ho₂O₃, In₂O₃, La₂O₃, Lu₂O₃, Nd₂O₃, Pr₂O₃, Sm₂O₃, Tb₂O₃, Tl₂O₃, Tm₂O₃, Y₂O₃ and Yb₂O₃.

5. (Original) The semiconductor apparatus according to claim 1, wherein the buffer layer is made of monocrystal SiGe.

6. (Original) The semiconductor apparatus according to claim 1, wherein the buffer layer is formed on the silicon substrate through the insulating film.

7. (Currently Amended) A semiconductor apparatus comprising:

a substrate;

a buffer layer made of a monocrystal semiconductor material and formed on the substrate;

a strained-silicon layer formed on the buffer layer and having a lattice constant different from that of the buffer layer;

a source region and a drain region formed in the strained-silicon layer so as to be separated from each other;

a gate insulating film formed on the strained-silicon layer sandwiched between the source region and the drain region and made of a monocrystal rare earth oxide having a lattice constant different from that of silicon; and

a monocrystal semiconductor gate electrode formed on the gate insulating film.

8. (Cancelled)

9. (Currently Amended) The semiconductor apparatus according to claim 7, wherein the gate electrode is made of ~~erystalline monocrystal~~ SiGe.

10. (Previously Presented) The semiconductor apparatus according to claim 7, wherein the gate insulating film is a monocrystal film including one selected from the group consisting of CeO₂, PrO₂, CaO₂, TbO₂, PrO₂, Dy₂O₃, Er₂O₃, Eu₂O₃, Gd₂O₃, Ho₂O₃, In₂O₃, La₂O₃, Lu₂O₃, Nd₂O₃, Pr₂O₃, Sm₂O₃, Tb₂O₃, Tl₂O₃, Tm₂O₃, Y₂O₃ and Yb₂O₃.

11. (Original) The semiconductor apparatus according to claim 7, wherein the buffer layer is made of monocrystal SiGe.

12. (Original) The semiconductor apparatus according to claim 7, wherein the buffer layer is formed on the silicon substrate through the insulating film.

13.-19. (Cancelled)